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U.S. Department of Commerce Patent and Trademark Office Information Disclosure Statement by Applicant		ATTY. DOCKET NUMBER HIRA.0204		Tollocal Spigged 49683			
		APPLICANT SUDA et al.					
		FILING DATE Concurrently	GROUP	GROUP			
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/MS/	09-181355	12/25/95	Japan			Abstract	x
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	nitial if citation is considere t in conformance and not co						hrough

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